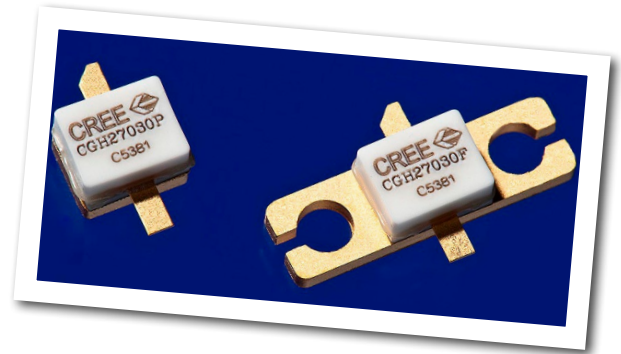


# CGH27030

## 30 W, 28V, GaN HEMT for Linear Communications ranging from VHF to 3 GHz

Cree's CGH27030 is a gallium nitride (GaN) high electron mobility transistor (HEMT) designed specifically for high efficiency, high gain and wide bandwidth capabilities, which makes the CGH27030 ideal for VHF, Comms, 3G, 4G, LTE, 2.3-2.9GHz WiMAX and BWA amplifier applications. The unmatched transistor is available in both screw-down, flange and solder-down, pill packages.



Package Type: 440196 and 440166  
PN: CGH27030P and CGH27030F

### Typical Performance Over 2.3-2.7GHz ( $T_c = 25^\circ\text{C}$ ) of Demonstration Amplifier

Parameter	2.3 GHz	2.4 GHz	2.5 GHz	2.6 GHz	2.7 GHz	Units
Small Signal Gain	15.6	15.5	15.3	15.1	15.2	dB
EVM at $P_{AVE} = 36 \text{ dBm}$	1.73	1.85	1.85	1.77	1.43	%
Drain Efficiency at 36 dBm	28.1	28.7	28.9	27.9	27.5	%
Input Return Loss	6.6	6.2	6.0	6.1	7.0	dB

**Note:**

Measured in the CGH27030F-AMP amplifier circuit, under 802.16 OFDM, 3.5 MHz Channel BW, 1/4 Cyclic Prefix, 64 QAM Modulated Burst, 5 ms Burst, Symbol Length of 59, Coding Type RS-CC, Coding Rate Type 2/3, PAR = 9.8 dB @ 0.01 % Probability on CCDF.

### Features



- VHF - 3.0 GHz Operation
- 30 W Peak Power Capability
- 15 dB Small Signal Gain
- 4.0 W  $P_{AVE}$  at < 2.0 % EVM
- 28 % Drain Efficiency at 4 W Average Power
- WiMAX Fixed Access 802.16-2004 OFDM
- WiMAX Mobile Access 802.16e OFDMA

Large Signal Models Available for ADS and MWO

## Absolute Maximum Ratings (not simultaneous) at 25°C Case Temperature

Parameter	Symbol	Rating	Units	Conditions
Drain-Source Voltage	$V_{DSS}$	84	Volts	25°C
Gate-to-Source Voltage	$V_{GS}$	-10, +2	Volts	25°C
Power Dissipation	$P_{DISS}$	14	Watts	
Storage Temperature	$T_{STG}$	-65, +150	°C	
Operating Junction Temperature	$T_J$	225	°C	
Maximum Forward Gate Current	$I_{GMAX}$	4.0	mA	25°C
Maximum Drain Current <sup>1</sup>	$I_{DMAX}$	3.0	A	25°C
Soldering Temperature <sup>2</sup>	$T_S$	245	°C	
Screw Torque	$\tau$	60	in-oz	
Thermal Resistance, Junction to Case <sup>3</sup>	$R_{\theta JC}$	4.8	°C/W	85°C
Case Operating Temperature <sup>3</sup>	$T_C$	-40, +150	°C	

Note:

<sup>1</sup> Current limit for long term, reliable operation.

<sup>2</sup> Refer to the Application Note on soldering at [www.cree.com/RF/Document-Library](http://www.cree.com/RF/Document-Library)

<sup>3</sup> Measured for the CGH27030F at  $P_{DISS} = 14$  W

## Electrical Characteristics ( $T_c = 25^\circ\text{C}$ )

Characteristics	Symbol	Min.	Typ.	Max.	Units	Conditions
<b>DC Characteristics<sup>1</sup></b>						
Gate Threshold Voltage	$V_{GS(th)}$	-3.8	-3.0	-2.3	$V_{DC}$	$V_{DS} = 10$ V, $I_D = 7.2$ mA
Gate Quiescent Voltage	$V_{GS(Q)}$	-	-2.7	-	$V_{DC}$	$V_{DS} = 28$ V, $I_D = 150$ mA
Saturated Drain Current	$I_{DS}$	5.8	7.0	-	A	$V_{DS} = 6.0$ V, $V_{GS} = 2$ V
Drain-Source Breakdown Voltage	$V_{BR}$	120	-	-	$V_{DC}$	$V_{GS} = -8$ V, $I_D = 7.2$ mA
<b>RF Characteristics<sup>2,3</sup> (<math>T_c = 25^\circ\text{C}</math>, <math>F_0 = 2.5</math> GHz unless otherwise noted)</b>						
Small Signal Gain	$G_{SS}$	12.5	14.5	-	dB	$V_{DD} = 28$ V, $I_{DQ} = 150$ mA
Drain Efficiency <sup>4</sup>	$\eta$	23.0	28.0	-	%	$V_{DD} = 28$ V, $I_{DQ} = 150$ mA, $P_{AVE} = 4$ W
Error Vector Magnitude	EVM	-	2.0	-		$V_{DD} = 28$ V, $I_{DQ} = 150$ mA, $P_{AVE} = 4$ W
Output Mismatch Stress	VSWR	-	-	10 : 1	Y	No damage at all phase angles, $V_{DD} = 28$ V, $I_{DQ} = 150$ mA $P_{AVE} = 4.0$ W OFDM $P_{AVE}$
<b>Dynamic Characteristics<sup>5</sup></b>						
Input Capacitance	$C_{GS}$	-	9.0	-	pF	$V_{DS} = 28$ V, $V_{gs} = -8$ V, $f = 1$ MHz
Output Capacitance	$C_{DS}$	-	2.6	-	pF	$V_{DS} = 28$ V, $V_{gs} = -8$ V, $f = 1$ MHz
Feedback Capacitance	$C_{GD}$	-	0.4	-	pF	$V_{DS} = 28$ V, $V_{gs} = -8$ V, $f = 1$ MHz

Notes:

<sup>1</sup> Measured on wafer prior to packaging.

<sup>2</sup> Measured in the CGH27030F-AMP test fixture.

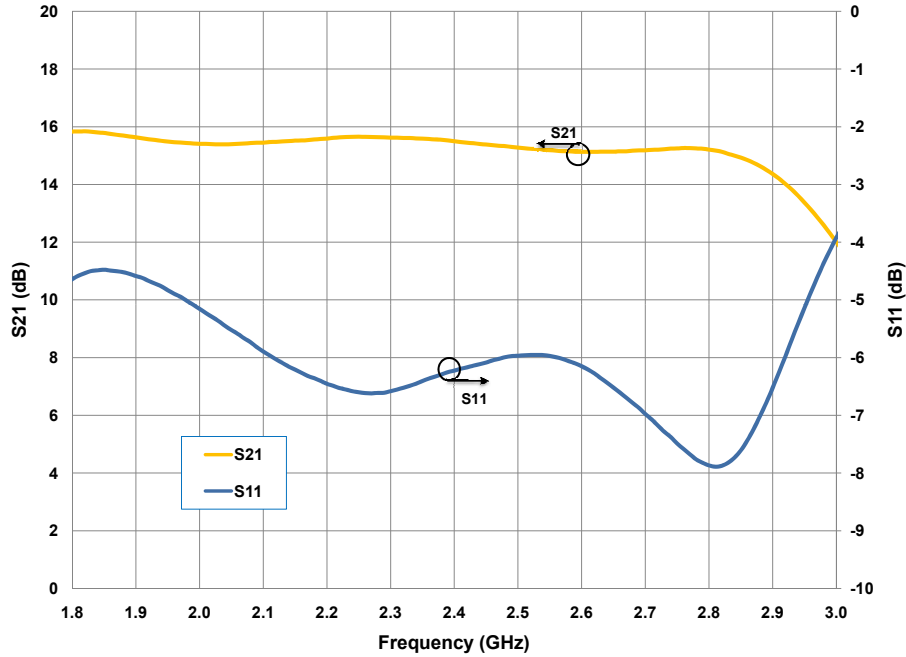
<sup>3</sup> Under 802.16 OFDM, 3.5 MHz Channel BW, 1/4 Cyclic Prefix, 64 QAM Modulated Burst, 5 ms Burst, Symbol Length of 59, Coding Type RS-CC, Coding Rate Type 2/3, PAR = 9.8 dB @ 0.01 % Probability on CCDF.

<sup>4</sup> Drain Efficiency =  $P_{out} / P_{dc}$ .

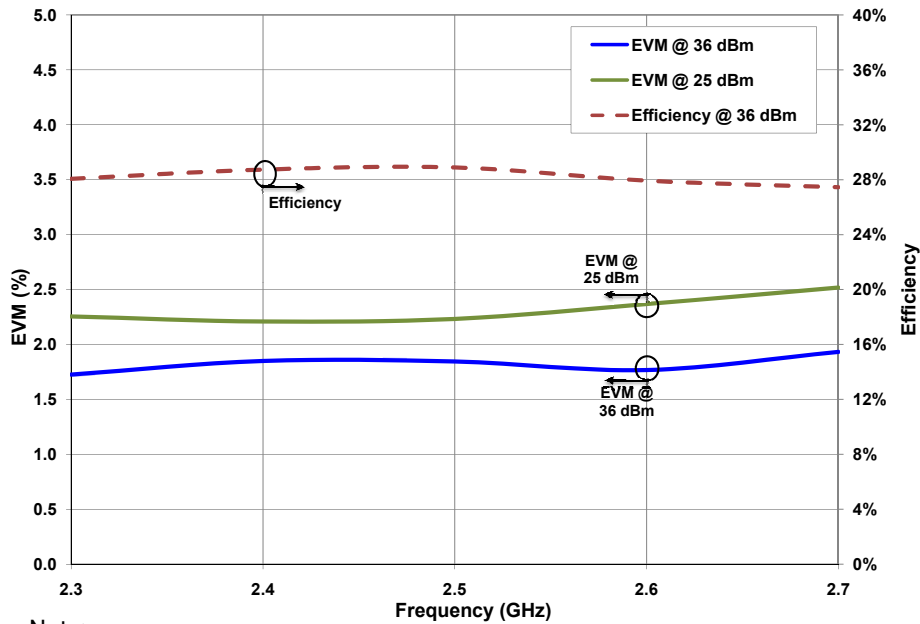
<sup>5</sup> Capacitance values include package parasitics.

## Typical WiMAX Performance

**Small Signal S-Parameters vs Frequency measured in CGH27030F-AMP**  
 $V_{DD} = 28\text{ V}$ ,  $I_{DQ} = 150\text{ mA}$



**Typical EVM and Efficiency versus Frequency measured in CGH27030F-AMP**  
 $V_{DD} = 28\text{ V}$ ,  $I_{DQ} = 150\text{ mA}$ , 802.16-2004 OFDM, PAR=9.8 dB,  $P_{AVE} = 5\text{ W}$

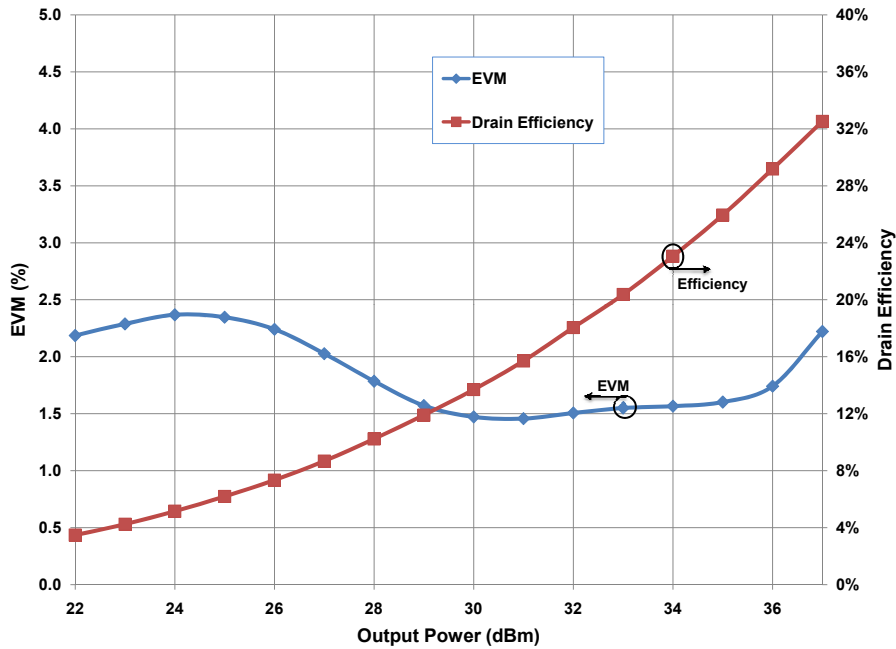


Note:

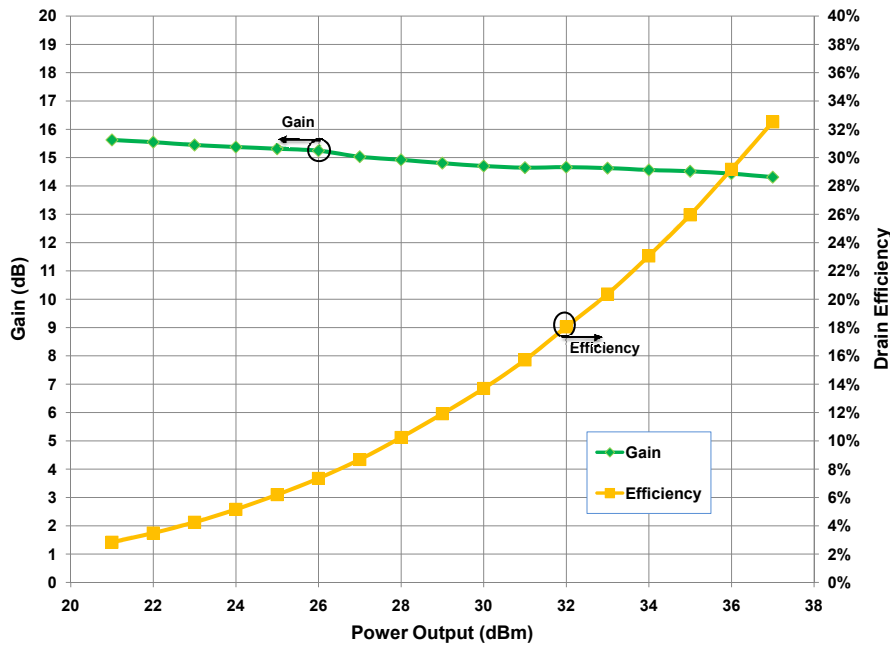
Under 802.16 OFDM, 3.5 MHz Channel BW, 1/4 Cyclic Prefix, 64 QAM Modulated Burst, Symbol Length of 59, Coding Type RS-CC, Coding Rate Type 2/3, PAR = 9.8 dB @ 0.01 % Probability on CCDF.

## Typical WiMAX Performance

**Drain Efficiency and EVM vs Output Power measured in CGH27030F-AMP**  
 $V_{DD} = 28\text{ V}$ ,  $I_{DQ} = 150\text{ mA}$ , 802.16-2004 OFDM, PAR = 9.8 dB



**Typical Gain and Efficiency versus Output Power measured in CGH27030F-AMP**  
 $V_{DD} = 28\text{ V}$ ,  $I_{DQ} = 150\text{ mA}$ , 802.16-2004 OFDM, PAR=9.8 dB

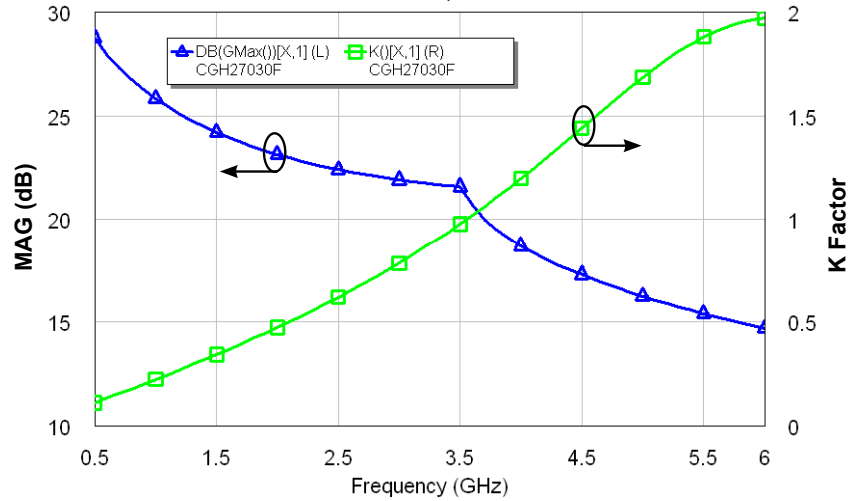


**Note:**

Under 802.16 OFDM, 3.5 MHz Channel BW, 1/4 Cyclic Prefix, 64 QAM Modulated Burst, Symbol Length of 59, Coding Type RS-CC, Coding Rate Type 2/3, PAR = 9.8 dB @ 0.01 % Probability on CCDF.

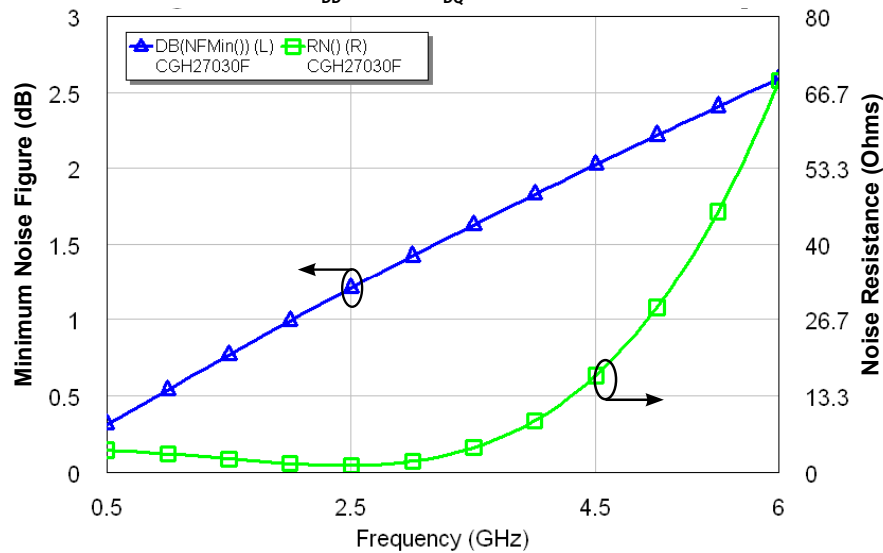
## Typical Performance Data

**Simulated Maximum Available Gain and K Factor of the CGH27030F**  
 $V_{DD} = 28\text{ V}, I_{DQ} = 150\text{ mA}$



## Typical Noise Performance

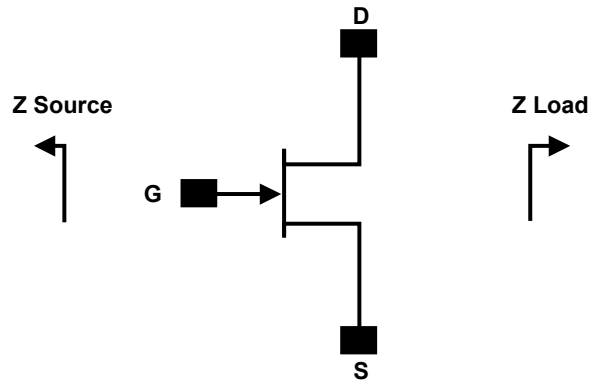
**Simulated Minimum Noise Figure and Noise Resistance vs Frequency of the CGH27030**  
 $V_{DD} = 28\text{ V}, I_{DQ} = 150\text{ mA}$



## Electrostatic Discharge (ESD) Classifications

Parameter	Symbol	Class	Test Methodology
Human Body Model	HBM	1A (> 250 V)	JEDEC JESD22 A114-D
Charge Device Model	CDM	II (200 < 500 V)	JEDEC JESD22 C101-C

## Source and Load Impedances



Frequency (MHz)	Z Source	Z Load
500	7.75 + j15.5	20 + j5.2
1000	3.11 + j5.72	17 + j6.66
1500	2.86 + j1.63	16.8 + j3.2
2500	1.2 - j3.26	9.41 + j3.2
3500	1.31 - j7.3	5.85 - j0.51

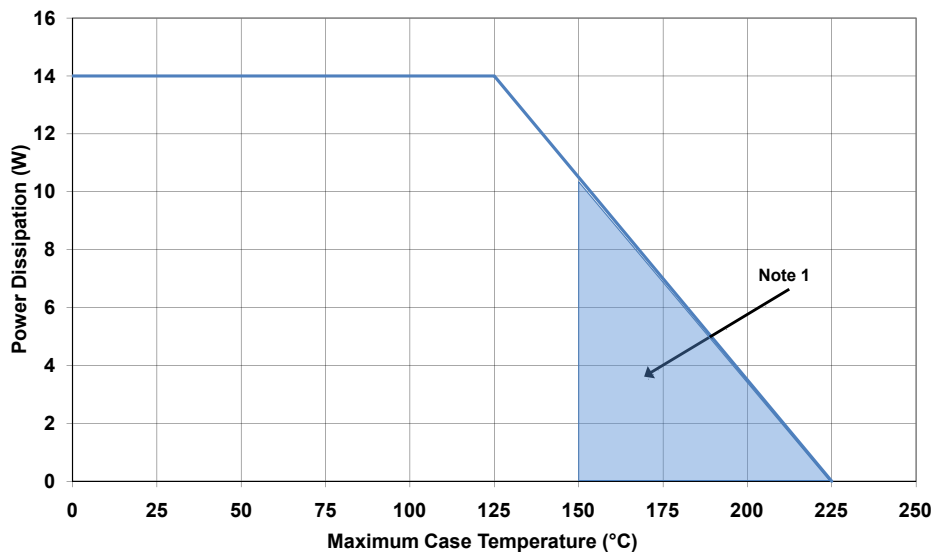
Note 1.  $V_{DD} = 28V$ ,  $I_{DQ} = 250mA$  in the 440166 package.

Note 2. Optimized for power gain,  $P_{SAT}$  and PAE.

Note 3. When using this device at low frequency, series resistors should be used to maintain amplifier stability.

## CGH27030 Power Dissipation De-rating Curve

CGH27030 Average Power Dissipation De-rating Curve



Note 1. Area exceeds Maximum Case Operating Temperature (See Page 2).

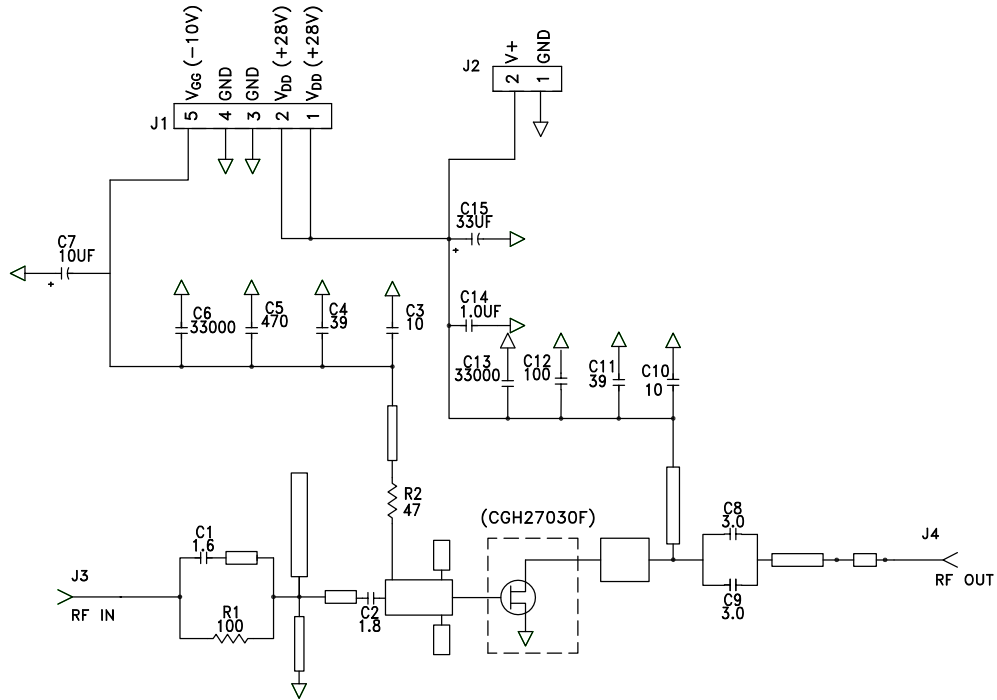
## CGH27030F-AMP Demonstration Amplifier Circuit Bill of Materials

Designator	Description	Qty
R1	RES,1/16W,0603,1%,100 OHMS	1
R2	RES,1/16W,0603,1%,47 OHMS	1
C5	CAP, 470PF, 5%,100V, 0603	1
C15	CAP, 33 UF, 20%, G CASE	1
C14	CAP, 1.0UF, 100V, 10%, X7R, 1210	1
C7	CAP 10UF 16V TANTALUM	1
C12	CAP, 100.0pF, +/-5%, 0603	1
C1	CAP, 1.6pF, +/-0.1pF, 0603	1
C2	CAP, 1.8pF, +/-0.1pF, 0603	1
C3,C10	CAP, 10.0pF,+/-5%, 0603	2
C4,C11	CAP, 39pF, +/-5%, 0603	2
C8,C9	CAP, 3.0pF, +/-0.1pF, 0603	2
C6,C13	CAP,33000PF, 0805,100V, X7R	2
J3,J4	CONN SMA STR PANEL JACK RECP	1
J2	HEADER RT>PLZ.1CEN LK 2 POS	1
J1	HEADER RT>PLZ. .1CEN LK 5POS	1
-	PCB, RO4350B, Er = 3.48, h = 20 mil	1
-	CGH27030F	1

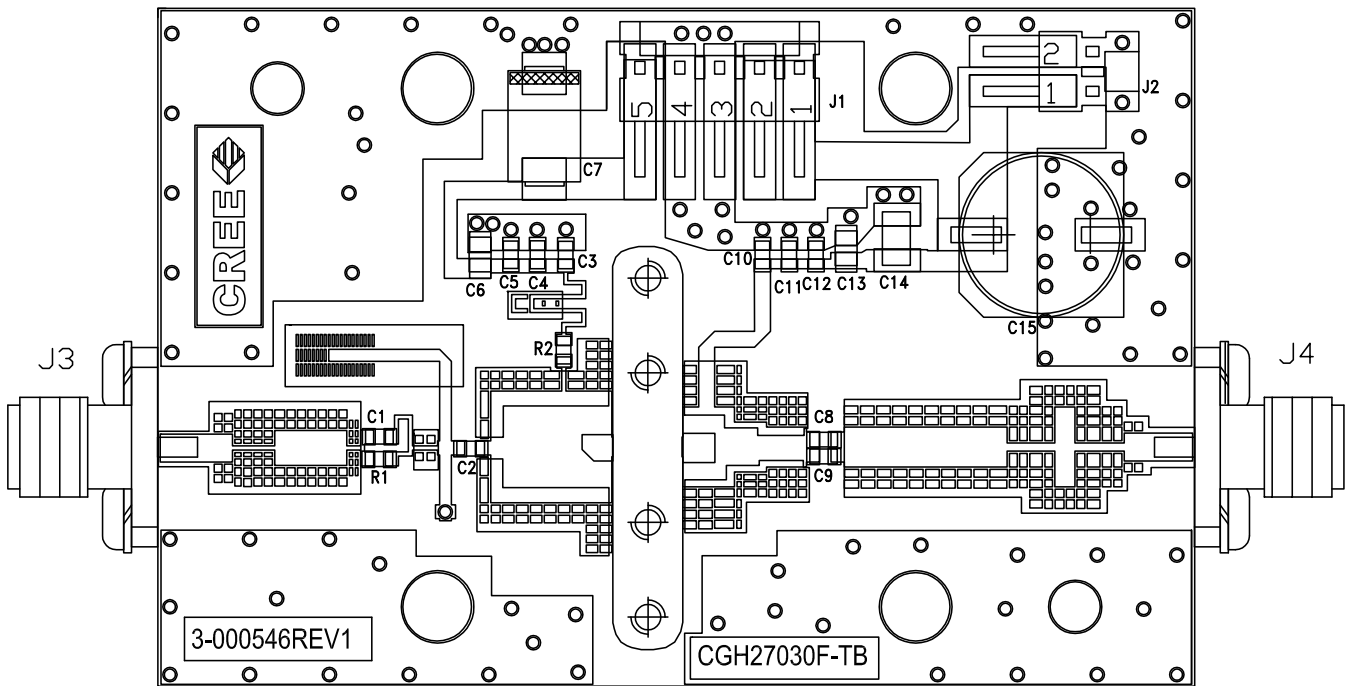
## CGH27030F-AMP Demonstration Amplifier Circuit



## CGH27030F-AMP Demonstration Amplifier Circuit Schematic



## CGH27030F-AMP Demonstration Amplifier Circuit Outline





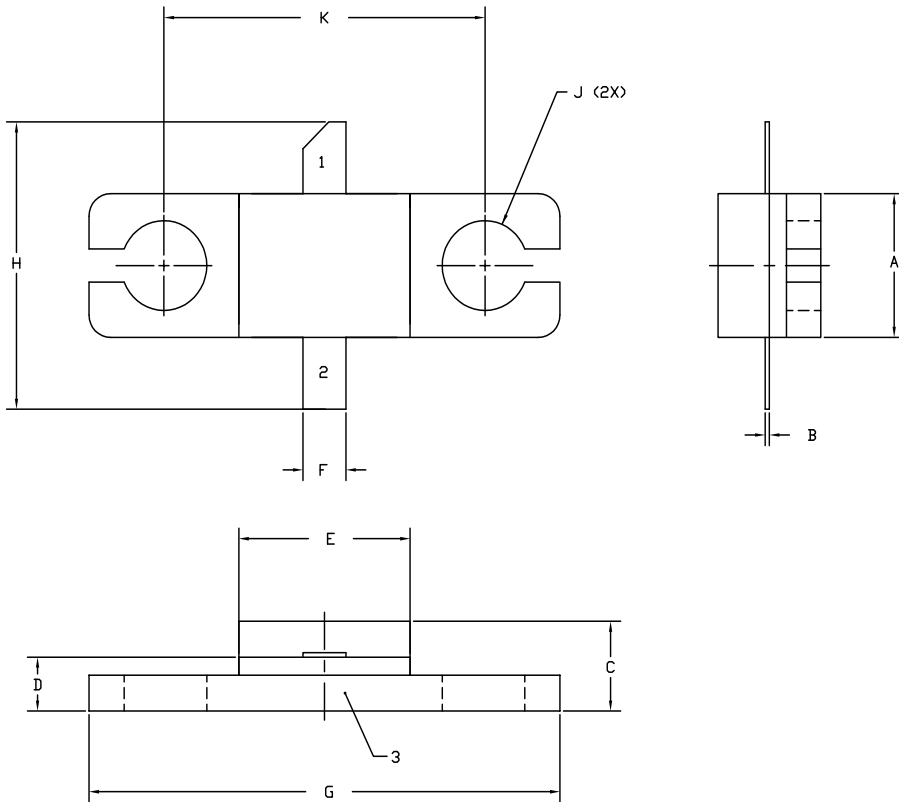


**Typical Package S-Parameters for CGH27030**  
 (Small Signal,  $V_{DS} = 28\text{ V}$ ,  $I_{DQ} = 150\text{ mA}$ , angle in degrees)

Frequency	Mag S11	Ang S11	Mag S21	Ang S21	Mag S12	Ang S12	Mag S22	Ang S22
500 MHz	0.910	-127.91	18.04	106.46	0.024	20.12	0.314	-103.83
600 MHz	0.904	-137.21	15.52	100.35	0.025	14.75	0.306	-111.67
700 MHz	0.900	-144.50	13.58	95.23	0.025	10.38	0.302	-117.66
800 MHz	0.897	-150.40	12.04	90.78	0.025	6.69	0.302	-122.33
900 MHz	0.895	-155.33	10.80	86.81	0.026	3.48	0.303	-126.06
1.0 GHz	0.894	-159.54	9.78	83.20	0.026	0.63	0.306	-129.12
1.1 GHz	0.893	-163.21	8.93	79.85	0.026	-1.95	0.310	-131.69
1.2 GHz	0.892	-166.46	8.22	76.69	0.025	-4.31	0.315	-133.89
1.3 GHz	0.891	-169.40	7.60	73.70	0.025	-6.51	0.321	-135.84
1.4 GHz	0.891	-172.09	7.07	70.84	0.025	-8.56	0.327	-137.59
1.5 GHz	0.891	-174.57	6.61	68.08	0.025	-10.50	0.334	-139.20
1.6 GHz	0.891	-176.88	6.20	65.41	0.025	-12.34	0.341	-140.70
1.7 GHz	0.891	-179.07	5.84	62.81	0.025	-14.09	0.348	-142.13
1.8 GHz	0.891	178.86	5.52	60.28	0.025	-15.76	0.355	-143.51
1.9 GHz	0.891	176.88	5.23	57.79	0.024	-17.36	0.362	-144.85
2.0 GHz	0.891	174.98	4.96	55.35	0.024	-18.90	0.370	-146.16
2.1 GHz	0.891	173.13	4.73	52.95	0.024	-20.38	0.378	-147.46
2.2 GHz	0.892	171.34	4.51	50.59	0.024	-21.80	0.385	-148.75
2.3 GHz	0.892	169.60	4.32	48.25	0.023	-23.16	0.393	-150.03
2.4 GHz	0.892	167.89	4.14	45.95	0.023	-24.48	0.400	-151.32
2.5 GHz	0.892	166.20	3.97	43.66	0.023	-25.74	0.408	-152.61
2.6 GHz	0.893	164.55	3.82	41.40	0.023	-26.95	0.415	-153.91
2.7 GHz	0.893	162.91	3.68	39.16	0.022	-28.11	0.422	-155.21
2.8 GHz	0.893	161.28	3.54	36.93	0.022	-29.22	0.429	-156.52
2.9 GHz	0.893	159.67	3.42	34.72	0.022	-30.28	0.436	-157.84
3.0 GHz	0.894	158.06	3.31	32.52	0.021	-31.28	0.443	-159.17
3.2 GHz	0.894	154.86	3.10	28.16	0.021	-33.13	0.456	-161.87
3.4 GHz	0.894	151.65	2.92	23.83	0.020	-34.76	0.469	-164.62
3.6 GHz	0.895	148.41	2.77	19.52	0.020	-36.15	0.480	-167.42
3.8 GHz	0.895	145.14	2.63	15.23	0.019	-37.28	0.491	-170.27
4.0 GHz	0.895	141.81	2.50	10.94	0.018	-38.13	0.501	-173.18
4.2 GHz	0.895	138.42	2.39	6.64	0.018	-38.69	0.510	-176.16
4.4 GHz	0.896	134.95	2.29	2.32	0.017	-38.93	0.519	-179.20
4.6 GHz	0.896	131.39	2.20	-2.02	0.017	-38.84	0.526	177.68
4.8 GHz	0.896	127.73	2.12	-6.40	0.016	-38.43	0.533	174.48
5.0 GHz	0.895	123.96	2.05	-10.82	0.016	-37.69	0.539	171.19
5.2 GHz	0.895	120.07	1.99	-15.29	0.016	-36.68	0.545	167.80
5.4 GHz	0.895	116.05	1.93	-19.83	0.016	-35.43	0.549	164.31
5.6 GHz	0.895	111.90	1.87	-24.44	0.016	-34.05	0.553	160.70
5.8 GHz	0.895	107.59	1.82	-29.13	0.016	-32.64	0.556	156.95
6.0 GHz	0.895	103.14	1.78	-33.91	0.016	-31.32	0.559	153.06

To download the s-parameters in s2p format, go to the [CGH27030 Product Page](#) and click on the documentation tab.

## Product Dimensions CGH27030F (Package Type – 440166)



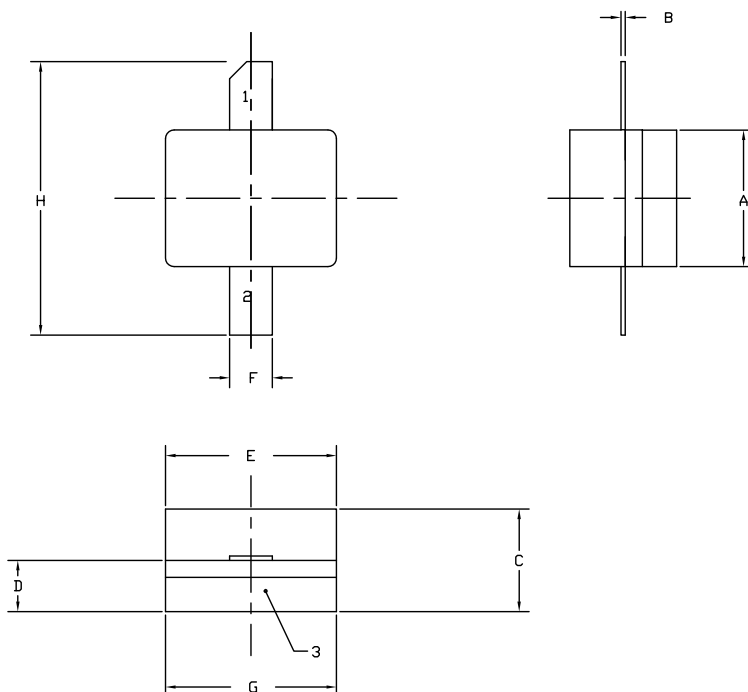
### NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. ADHESIVE FROM LID MAY EXTEND A MAXIMUM OF 0.020" BEYOND EDGE OF LID.
4. LID MAY BE MISALIGNED TO THE BODY OF THE PACKAGE BY A MAXIMUM OF 0.008" IN ANY DIRECTION.
5. ALL PLATED SURFACES ARE NI/AU

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.155	0.165	3.94	4.19
B	0.004	0.006	0.10	0.15
C	0.115	0.135	2.92	3.43
D	0.057	0.067	1.45	1.70
E	0.195	0.205	4.95	5.21
F	0.045	0.055	1.14	1.40
G	0.545	0.555	13.84	14.09
H	0.280	0.360	7.11	9.14
J	Ø .100		2.54	
K	0.375		9.53	

- PIN 1. GATE  
 PIN 2. DRAIN  
 PIN 3. SOURCE

## Product Dimensions CGH27030P (Package Type – 440196)



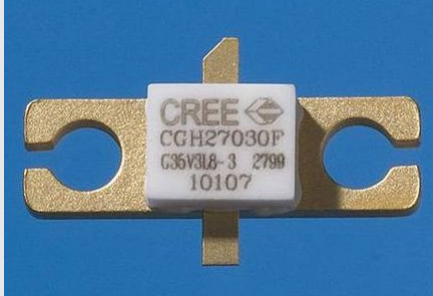

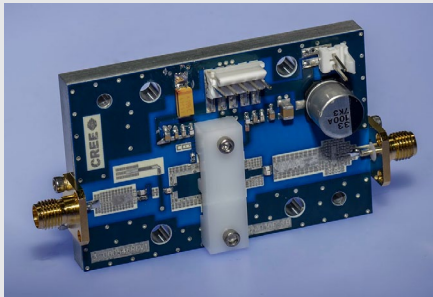
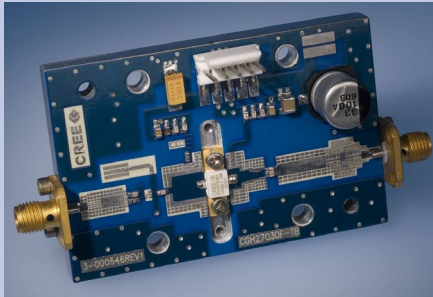
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DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.155	0.165	3.94	4.19
B	0.003	0.006	0.10	0.15
C	0.115	0.135	2.92	3.17
D	0.057	0.067	1.45	1.70
E	0.195	0.205	4.95	5.21
F	0.045	0.055	1.14	1.40
G	0.195	0.205	4.95	5.21
H	0.280	0.360	7.11	9.14

- PIN 1. GATE  
 PIN 2. DRAIN  
 PIN 3. SOURCE

## Product Ordering Information

Order Number	Description	Unit of Measure	Image
CGH27030F	GaN HEMT	Each	 <p>A photograph of a GaN HEMT device (CGH27030F) mounted on a gold-colored metal carrier. The carrier has two large circular cutouts on either side. The device is a small white rectangular chip with gold wire bonds. The chip is labeled with 'CREE', 'CGH27030F', 'G36V3L8-3 2799', and '10107'.</p>
CGH27030P	GaN HEMT	Each	 <p>A photograph of a GaN HEMT device (CGH27030P) mounted on a gold-colored metal carrier. The carrier has two large circular cutouts on either side. The device is a small white rectangular chip with gold wire bonds. The chip is labeled with 'CREE', 'CGH27030P', and 'C5381'.</p>
CGH27030F-TB	Test board without GaN HEMT	Each	 <p>A photograph of a test board (CGH27030F-TB) without the GaN HEMT device installed. The board is blue and populated with various electronic components, including a large silver capacitor, several resistors, and integrated circuits. It has two SMA connectors on the left and right sides.</p>
CGH27030F-AMP	Test board with GaN HEMT installed	Each	 <p>A photograph of a test board (CGH27030F-AMP) with the GaN HEMT device installed. The board is blue and populated with various electronic components, including a large silver capacitor, several resistors, and integrated circuits. It has two SMA connectors on the left and right sides.</p>



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В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

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